

IN THE SPECIFICATION:

Please replace the following paragraph at page 10, line 5.

The preferred plating system 10 comprises an electroplating tank 11 (also known as the holding tank) which holds copper electrolyte 27 and which is made of a suitable material such as plastic or other material inert to the electrolytic plating solution. The tank is preferably cylindrical especially for wafer plating. A cathode 12 is horizontally disposed at the upper part of tank 11 and may be any type substrate such as a silicon wafer having openings such as trenches and vias. The wafer substrate 12a is typically coated with a seed layer of copper or other metal to initiate plating thereon. A copper seed layer may be applied by CVD, PVD, or the like. An anode 13 is also preferably circular for wafer plating and is horizontally disposed at the lower part of tank 11 forming a space between the anode 13 and cathode 12. The anode 13 is typically a soluble anode, but may also be an insoluble anode which is not consumed in the process.